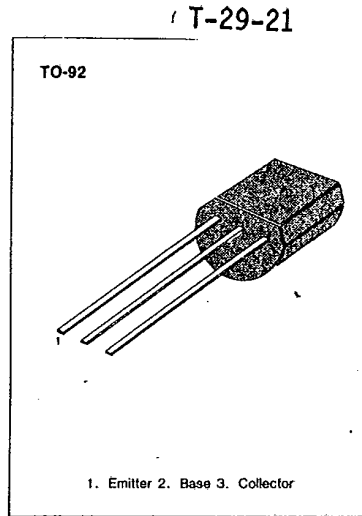


**MPS6601****NPN EPITAXIAL SILICON TRANSISTOR****AMPLIFIER TRANSISTOR**

- Collector-Emitter Voltage:  $V_{CE0} = 25V$
- Collector Dissipation:  $P_C (\text{max}) = 625mW$

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ C$ )**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	25	V
Collector-Emitter Voltage	$V_{CEO}$	25	V
Emitter-Base Voltage	$V_{EBO}$	4	V
Collector Current	$I_C$	1000	mA
Collector Dissipation	$P_C$	625	mW
Junction Temperature	$T_J$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 ~ 150	$^\circ C$

**ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )**

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	$I_C = 1mA, I_B = 0$	25			V
Collector-Base Breakdown Voltage	$BV_{CBO}$	$I_C = 100\mu A, I_E = 0$	25			V
Emitter Base Breakdown Voltage	$BV_{EBO}$	$I_E = 10\mu A, I_C = 0$	4			V
Collector Cut-off Current	$I_{CEO}$	$V_{CE} = 25V, I_B = 0$			100	nA
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 25V, I_E = 0$			100	nA
DC Current Gain	$h_{FE}$	$I_C = 100mA, V_{CE} = 1V$	50			
		$I_C = 500mA, V_{CE} = 1V$	50			
		$I_C = 1000mA, V_{CE} = 1V$	30			
Collector-Emitter Saturation Voltage	$V_{CE} (\text{sat})$	$I_C = 1000mA, I_B = 100mA$			0.6	V
Current Gain Bandwidth Product	$f_T$	$I_C = 50mA, V_{CE} = 10V$	100			MHz
		$f = 30MHz$				
Output Capacitance	$C_{ob}$	$V_{CB} = 10V, I_E = 0$			30	pF
		$f = 100KHz$				

MPS6601

NPN EPITAXIAL SILICON TRANSISTOR

T-29-21

